MCH6342-TL-W Datasheet

https://www.DiGi-Electronics.com

DiGi Electronics Part Number	MCH6342-TL-W-DG
Manufacturer	onsemi
Manufacturer Product Number	MCH6342-TL-W
Description	MOSFET P-CH 30V 4.5A MCPH6
Detailed Description	P-Channel 30 V 4.5A (Ta) 1.5W (Ta) Surface Mount SC-88FL/MCPH6

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
MCH6342-TL-W	onsemi
Series:	Product Status:
-	Obsolete
FET Type:	Technology:
P-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
30 V	4.5A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
1.8V, 4.5V	73mOhm @ 2A, 4.5V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
1.3V @ 1mA	8.6 nC @ 4.5 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±10V	650 pF @ 10 V
FET Feature:	Power Dissipation (Max):
-	1.5W (Ta)
Operating Temperature:	Mounting Type:
150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
SC-88FL/MCPH6	6-TSSOP, SC-88, SOT-363
Base Product Number:	
MCH6342	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	

MCH6342

Power MOSFET
–30V, 73mΩ, –4.5A, Single P-Channel

ON Semiconductor®

www.onsemi.com

This Power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and low on resistance. This device is suitable for applications with low gate charge driving or low on resistance requirements.

Features

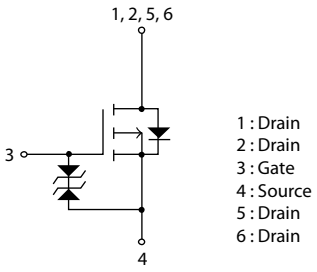
- Low On-Resistance
- 1.8V drive
- High Speed Switching
- ESD Diode-Protected Gate
- Pb-Free, Halogen Free and RoHS compliance

Typical Applications

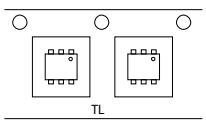
- DC/DC Converter

V_{DSS}	R_{DS}(on) Max	I_D Max
–30V	73mΩ@ –4.5V	–4.5A
	99mΩ@ –2.5V	
	155mΩ@ –1.8V	

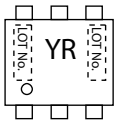
ELECTRICAL CONNECTION
P-Channel



PACKING TYPE : TL



MARKING



ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

SPECIFICATIONS

ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit
Drain to Source Voltage	V_{DSS}	–30	V
Gate to Source Voltage	V_{GSS}	±10	V
Drain Current (DC)	I_D	–4.5	A
Drain Current (Pulse) PW ≤ 10μs, duty cycle ≤ 1%	I_{DP}	–18	A
Power Dissipation When mounted on ceramic substrate (1500mm^2 × 0.8mm)	P_D	1.5	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	–55 to +150	°C

Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate (1500mm^2 × 0.8mm)	$R_{\theta JA}$	83.3	°C/W

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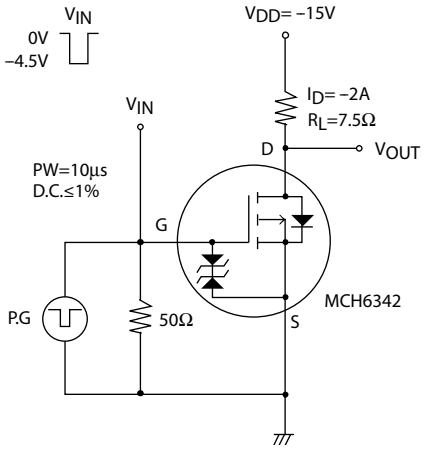
ELECTRICAL CHARACTERISTICS at Ta = 25°C (Note 2)

Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=−1mA, V_{GS}=0V	−30			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=−30V, V_{GS}=0V			−1	μA
Gate to Source Leakage Current	I_{GSS}	V_{GS}=±8V, V_{DS}=0V			±10	μA
Gate Threshold Voltage	$V_{GS}(th)$	V_{DS}=−10V, I_D=−1mA	−0.4		−1.3	V
Forward Transconductance	g_{FS}	V_{DS}=−10V, I_D=−2A	3.4	5.8		S
Static Drain to Source On-State Resistance	$R_{DS}(on)1$	I_D=−2A, V_{GS}=−4.5V		56	73	mΩ
	$R_{DS}(on)2$	I_D=−1A, V_{GS}=−2.5V		71	99	mΩ
	$R_{DS}(on)3$	I_D=−0.3A, V_{GS}=−1.8V		95	155	mΩ
Input Capacitance	Ciss	V_{DS}=−10V, f=1MHz		650		pF
Output Capacitance	Coss			105		pF
Reverse Transfer Capacitance	Crss			83		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit		8.2		ns
Rise Time	t_r			28		ns
Turn-OFF Delay Time	$t_d(off)$			100		ns
Fall Time	t_f			60		ns
Total Gate Charge	Qg	V_{DS}=−15V, V_{GS}=−4.5V, I_D=−4.5A		8.6		nC
Gate to Source Charge	Qgs			1.3		nC
Gate to Drain “Miller” Charge	Qgd			2.4		nC
Forward Diode Voltage	V_{SD}	I_S=−4.5A, V_{GS}=0V		−0.83	−1.2	V

Note 2 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit



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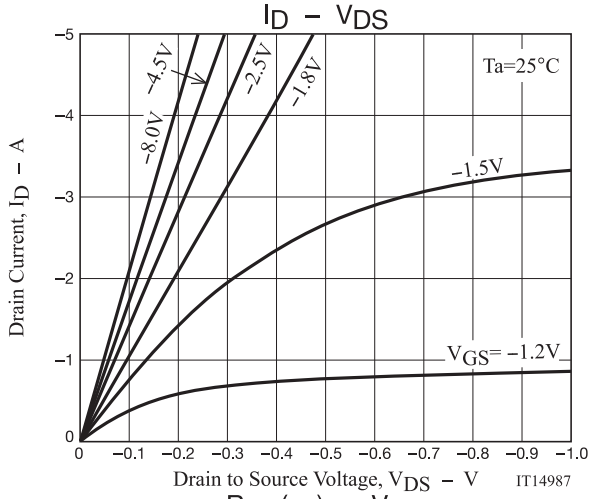
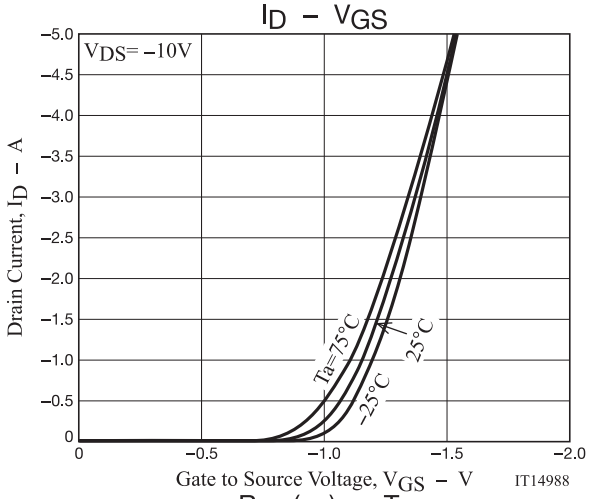
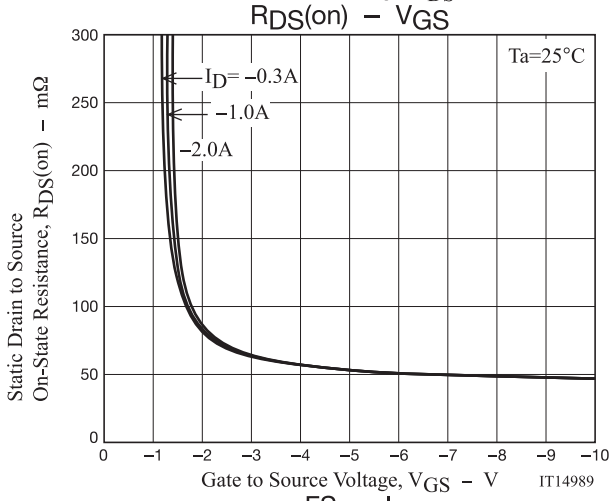
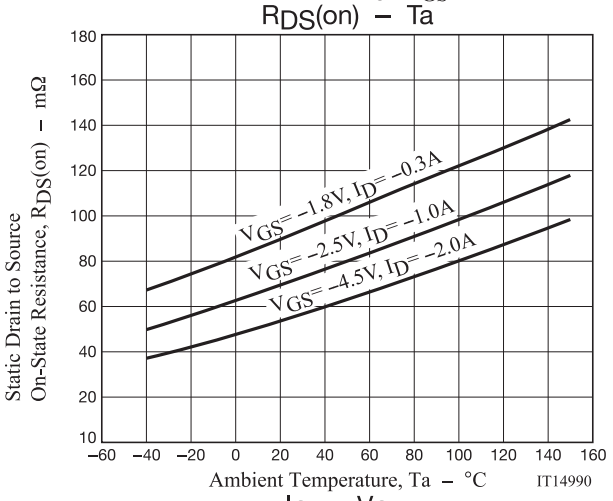
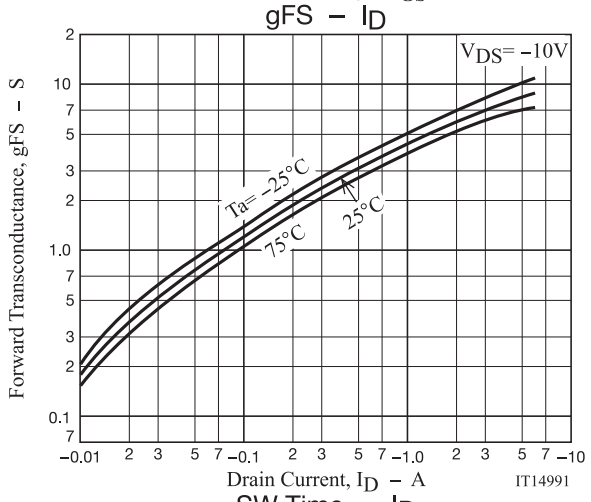
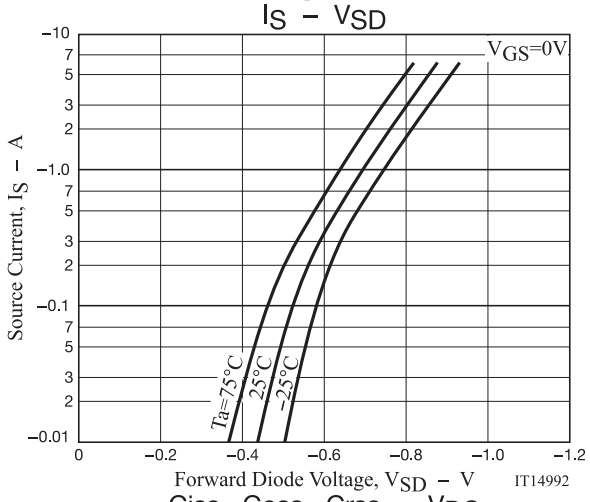

ID – VDS
Ta=25°C
–4.5V
–2.5V
–1.8V
–8.0V
–1.5V
VGS= –1.2V
Drain Current, ID – A
Drain to Source Voltage, VDS – V
IT14987

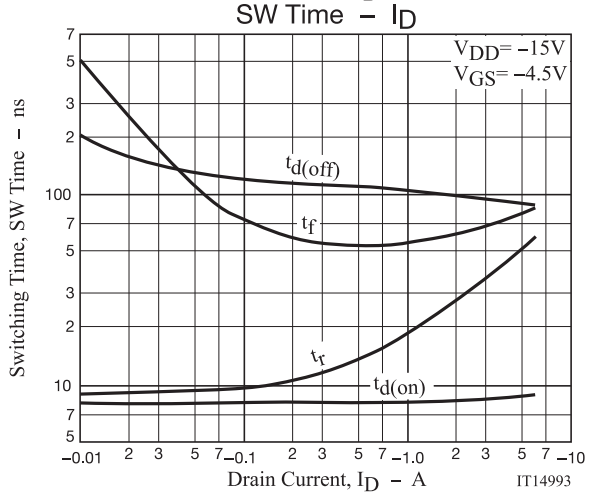

ID – VGS
VDS= –10V
Ta=75°C
25°C
–25°C
Drain Current, ID – A
Gate to Source Voltage, VGS – V
IT14988

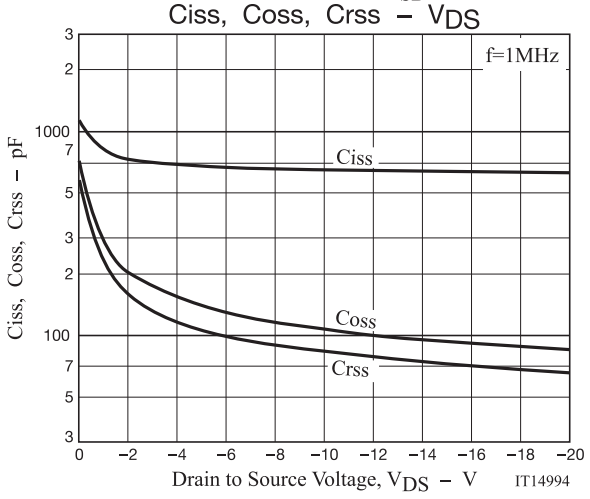

RDS(on) – VGS
Ta=25°C
ID= –0.3A
–1.0A
–2.0A
Static Drain to Source On-State Resistance, RDS(on) – mΩ
Gate to Source Voltage, VGS – V
IT14989


RDS(on) – Ta
VGS= –1.8V, ID= –0.3A
VGS= –2.5V, ID= –1.0A
VGS= –4.5V, ID= –2.0A
Static Drain to Source On-State Resistance, RDS(on) – mΩ
Ambient Temperature, Ta – °C
IT14990


gFS – ID
VDS= –10V
Ta= –25°C
25°C
75°C
Forward Transconductance, gFS – S
Drain Current, ID – A
IT14991


IS – VSD
VGS=0V
Ta=75°C
25°C
–25°C
Source Current, IS – A
Forward Diode Voltage, VSD – V
IT14992


SW Time – ID
VDD= –15V
VGS= –4.5V
td(off)
tf
tr
td(on)
Switching Time, SW Time – ns
Drain Current, ID – A
IT14993


Ciss, Coss, Crss – VDS
f=1MHz
Ciss
Coss
Crss
Ciss, Coss, Crss – pF
Drain to Source Voltage, VDS – V
IT14994

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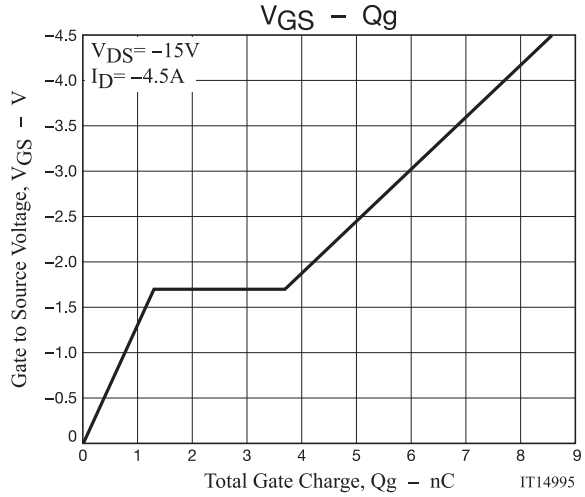
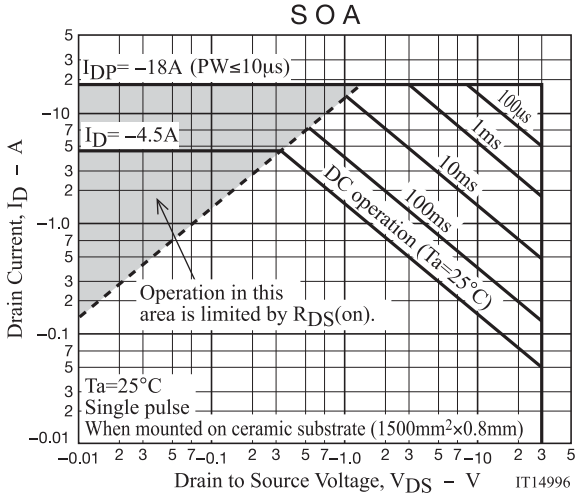
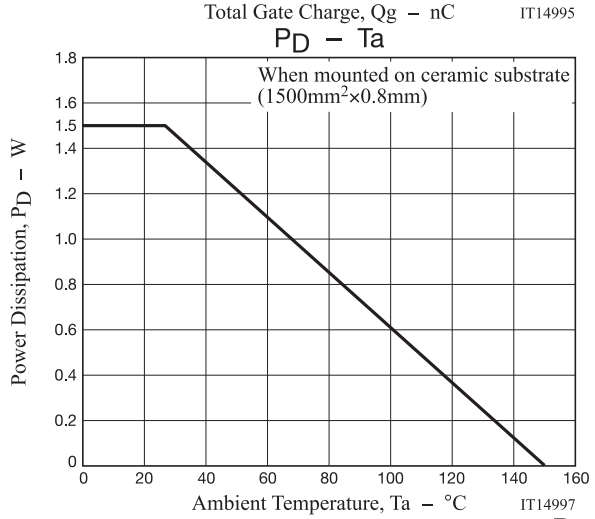
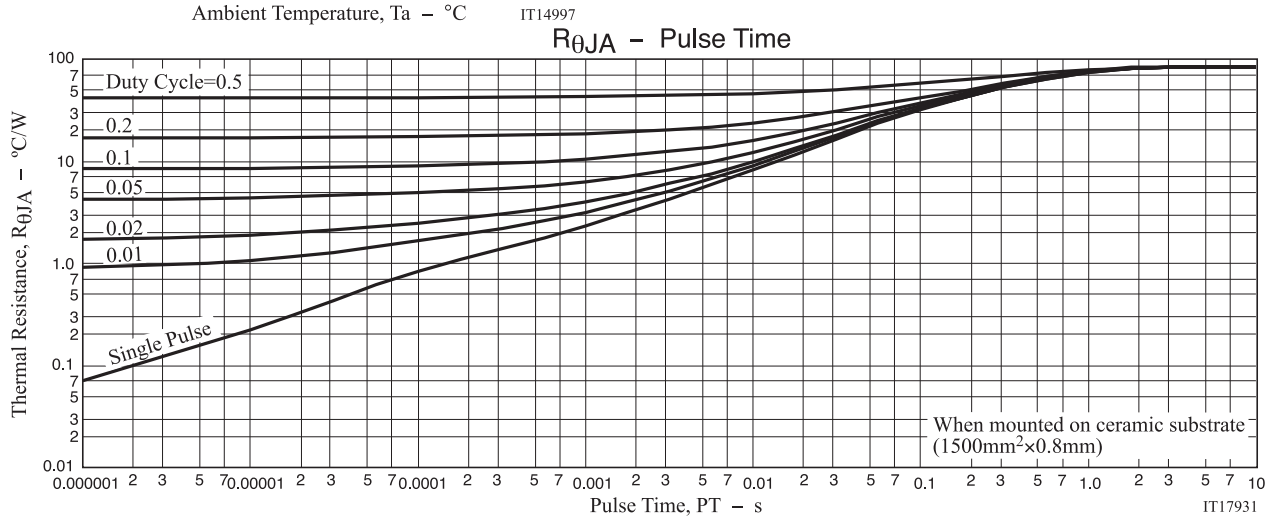

VGS – Qg
VDS= –15V
ID= –4.5A
Gate to Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT14995


S O A
IDP= –18A (PW≤10μs)
ID= –4.5A
100μs
1ms
10ms
100ms
DC operation (Ta=25°C)
Operation in this
area is limited by RDS(on).
Ta=25°C
Single pulse
When mounted on ceramic substrate (1500mm2×0.8mm)
Drain Current, ID – A
Drain to Source Voltage, VDS – V
IT14996


PD – Ta
When mounted on ceramic substrate
(1500mm2×0.8mm)
Power Dissipation, PD – W
Ambient Temperature, Ta – °C
IT14997

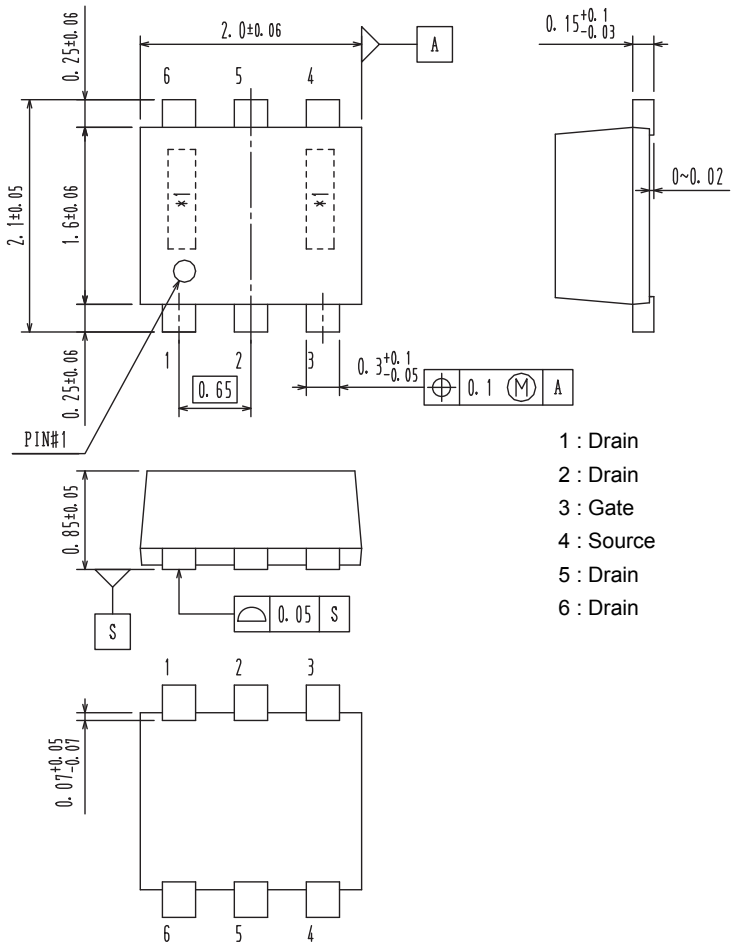

RθJA – Pulse Time
Duty Cycle=0.5
0.2
0.1
0.05
0.02
0.01
Single Pulse
When mounted on ceramic substrate
(1500mm2×0.8mm)
Thermal Resistance, RθJA – °C/W
Pulse Time, PT – s
IT17931

MCH6342

PACKAGE DIMENSIONS

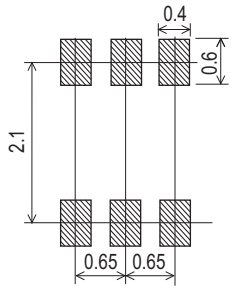
unit : mm

SC-88FL / MCPH6
CASE 419AS
ISSUE O



1 : Drain
2 : Drain
3 : Gate
4 : Source
5 : Drain
6 : Drain

Recommended Soldering Footprint



ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing)
MCH6342-TL-H	YR	SC-88FL / MCPH6 (Pb-Free / Halogen Free)	3,000 / Tape & Reel
MCH6342-TL-W			

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

Note on usage : Since the MCH6342 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

OUR CERTIFICATE

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